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IN THE CLAIMS

1. (currently amended): A semiconductor device,  
comprising:

a semiconductor substrate having a surface formed with  
a first recessed region;

a first dielectric material deposited in the first  
recessed region and formed with a second recessed region  
having walls; and

a semiconductor layer formed in proximity to the  
second recessed region; and

a thermal oxide layer formed integral with the  
semiconductor layer, wherein the thermal oxide layer seals  
the second recessed region while leaving a void in the  
second recessed region. ~~second dielectric material formed  
over the first dielectric material by thermally oxidizing a  
semiconductor cap layer formed above the first dielectric  
material and adjacent to the second recessed region to seal  
the second recessed region.~~

2. (original): The semiconductor device of claim 1,  
further comprising an active device formed in an active  
region of the semiconductor substrate.

3. (original): The semiconductor device of claim 1,  
further comprising an electrical component formed over the  
second recessed region.

4. (original): The semiconductor device of claim 3,  
wherein the electrical component comprises a passive device  
or bonding pad of the semiconductor device.

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5. (currently amended): The semiconductor device of claim 1, wherein the semiconductor layer comprises polysilicon. ~~second dielectric material is formed by thermally oxidizing a polysilicon cap layer.~~

6. (original): The semiconductor device of claim 1, wherein the first dielectric material includes deposited silicon dioxide.

7. (original): The semiconductor device of claim 1, wherein the second recessed region is formed having a third dielectric material deposited on the walls.

8. (currently amended): The semiconductor device of claim 1, wherein the first dielectric material is recessed below a major surface of the semiconductor substrate. ~~second dielectric material is formed with thermally grown silicon dioxide.~~

9. (currently amended): The semiconductor device of claim [[1,]] 8, wherein the first dielectric material is recessed below the major surface a distance of about 0.5 microns. ~~a portion of the semiconductor cap layer remains above the first dielectric material.~~

10. (currently amended): The semiconductor device of claim [[1,]] 7, wherein the third dielectric layer comprises polysilicon. ~~all of the semiconductor cap layer is oxidized to form the second dielectric material.~~

11. (currently amended): The semiconductor device of claim [[1,]] 7, wherein the third dielectric layer comprises amorphous silicon. ~~second recessed region extends into the~~

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~~semiconductor substrate to the depth of at least five micrometers.~~

Claims 12-25 (cancelled).

26. (currently amended): A semiconductor device, comprising:

a semiconductor substrate having a surface formed with a first recessed region;

a first dielectric material deposited in the first recessed region and formed with a second recessed region having an opening and walls; and

a semiconductor cap layer formed adjacent the opening;  
and

~~a second dielectric material thermally thermal oxide layer grown on the first semiconductor layer semiconductor layer to form a seal within the opening, wherein the seal is formed by converting at least a portion of a semiconductor cap layer to the second dielectric material, and wherein the semiconductor cap layer is formed adjacent the opening prior to forming the seal.~~

27. (previously presented): The semiconductor device of claim 26, wherein the semiconductor cap layer comprises polysilicon.

28. (currently amended): The semiconductor device of claim 27, wherein the ~~second dielectric material~~ thermal oxide layer includes thermally grown silicon dioxide.

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29. (previously presented): The semiconductor device of claim 26, further comprising an active device formed in an active region of the semiconductor substrate.
30. (previously presented): The semiconductor device of claim 26, further comprising an electrical component formed over the second recessed region.
31. (previously presented): The semiconductor device of claim 30, wherein the electrical component comprises a passive device or bonding pad of the semiconductor device.
32. (previously presented): The semiconductor device of claim 26, wherein the second recessed region is formed having a third dielectric material deposited on the walls.
33. (currently amended): The semiconductor device of claim 32, wherein the third dielectric material includes one of polysilicon and amorphous silicon. ~~silicon nitride.~~